IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

AKRAM ALI SALMAN XUEJUN ZHAO KURT O. TAYLOR STEPHEN G. BEEBE

Serial No.: Unknown

Filed: Concurrently Herewith

For: METHOD FOR DETERMINING THE

RELIABILITY OF DIELECTRIC LAYERS

Group Art Unit: Unknown

Examiner: Unknown

Attorney Docket: 2000.111200/H2022

Customer No.: 23720

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

NUMBER: EV 291395941 US

DATE OF DEPOSIT: September 18, 2003
I hereby certify that this paper or fee is being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 370 F.R. 1.10 on the date indicated above and is addressed to: Mail Stop Faten, Application, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed on attached Form PTO-1449 be considered by the Examiner and made of record. Copies of the listed documents required by 37 C.F.R. § 1.98(a)(2) are enclosed for the convenience of the Examiner.

In accordance with 37 C.F.R §§ 1.97(g),(h), this Information Disclosure Statement is not to be construed as a representation that a search has been made, and is not to be construed to be an admission that the information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b).

The present Information Disclosure Statement is being filed prior to the receipt of a first Official Action reflecting an examination on the merits, and hence is believed to be timely filed in accordance with 37 C.F.R § 1.97(b). No fees are believed to be due in connection with the filing of this Information Disclosure Statement, however, should any fees under 37 C.F.R. §§ 1.16 to 1.21 be deemed necessary for any reason relating to these materials, the Assistant Commissioner is hereby authorized to deduct said fees from Williams, Morgan & Amerson, P.C., Deposit Account No. 50-0786/2000.111200.

Applicants respectfully request that the listed documents be made of record in the present case.

Respectfully submitted,

WILLIAMS, MORGAN & AMERSON

CUSTOMER NO. 23720

Date: September 18, 2003

J. Mike Amerson

Reg. No. 35,426

10333 Richmond, Suite 1100

Houston, Texas 77042

(713) 934-4055

(713) 934-7011 (facsimile)

ATTORNEY FOR APPLICANTS

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Form D7	 ΓΟ-1449	(modified)		Atty. Docket N	Atty. Docket No.		Serial No.	
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List of Pa	tents and	Publications for	Applicant's	Applicant Akram Ali Salman, Xuejun Zhao, Kurt O. Taylor and				
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U.S	S. Patent I	Documents	Foreign Patent Document		ts	Other Art		
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	C1	Salman et al., "Gate Dielectric Breakdown and Latent Failures of Ultrathin (~13A) DPN under Pulsed Stress in Partially Depleted SOI MOSFETs"						
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	C3	Montoya et al., "A Study of the Mechanisms for ESD Damage to Reticles," EOS/ESD Symposium 00-394-405						
	C4	Hunter, "The Analysis of Oxide Reliability Data," 98 IRW Final Report, 114-34						
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Examiner:	DATE CONSIDERED:			
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EXAMINER: INITIAL IF REFERENCE CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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Linder et al., "Growth and Scaling of Oxide Conduction after Breakdown," 2003 IEEE, 402-05

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